

Silicon NPN Power Transistors

BU536

DESCRIPTION

- With TO-3 package
- High voltage
- Fast switching speed

APPLICATIONS

- For color TV horizontal deflection circuits.

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

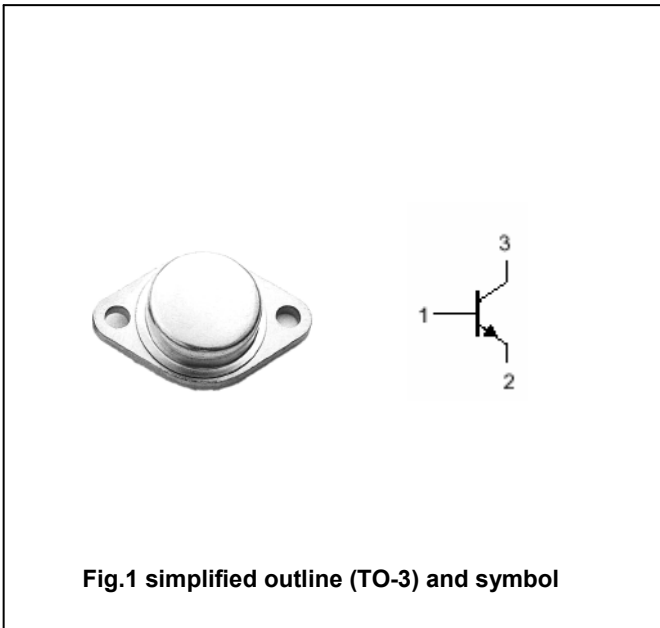


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1100	V
V _{CEO}	Collector-emitter voltage	Open base	480	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		8	A
I _{CM}	Collector current-peak	t _p <5ms	15	A
P _T	Total power dissipation	T _C =25□	62	W
T _j	Junction temperature		175	□
T _{stg}	Storage temperature		-65~175	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	1.0	□/W

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =100mA; I _B =0;	480			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA; I _C =0;	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A; I _B =0.8A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4A; I _B =0.8A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =1100V; I _E =0			1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	mA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	10			
h _{FE-2}	DC current gain	I _C =4A ; V _{CE} =5V	6.5			

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PACKAGE OUTLINE

